

ABSTRACT

According to one embodiment, a memory device includes
a substrate; a structure including a plurality of
5 conductive layers stacked on the substrate; and a pillar
arranged inside the structure and including a semiconductor
layer that extends in a direction perpendicular to a
surface of the substrate. The semiconductor layer includes
a first portion on a side of an upper portion of the
10 structure, and a second portion between the first portion
and the substrate. The first portion has a thickness larger
than a thickness of the second portion.